

## General Description

The WSF40130 is the highest performance trench MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSF40130 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

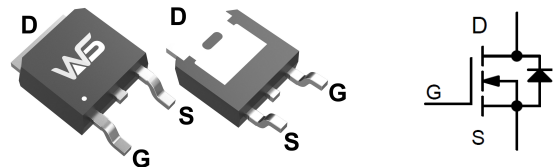
## Product Summary

BVDSS	RDSON	ID
40V	2.4mΩ	120A

## Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Power Tool Application

## TO-252 Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	40	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	120	A
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	79	A
I <sub>DM</sub>	Pulsed Drain Current <sup>a</sup>	360	A
EAS	Single Pulse Avalanche Energy <sup>b</sup>	400	mJ
I <sub>AS</sub>	Avalanche Current	40	A
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation	125	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>	---	62	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	1.0	°C/W

Notes :

- \* Avalanche single pulse test and avalanche period time  $t_{av} \leq 100 \mu s$ , duty < 1% . \*\*  
 Avalanche test condition: T<sub>J</sub>=25°C, L=0.5mH, I<sub>AS</sub>=40A, V<sub>DD</sub>=20V, and V<sub>GS</sub> = 10V. \*\*\*  
 Current limited by bond wire.

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.043	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	---	2.4	3.5	mΩ
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	3.2	5.0	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.3	1.8	2.6	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-6.94	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =32V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	2	uA
		V <sub>DS</sub> =32V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	10	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =20A	40	---	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	1.5	2	Ω
Q <sub>g</sub>	Total Gate Charge (10V)	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =40A	---	59	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	9.8	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	9.5	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =20V, V <sub>GEN</sub> =10V, R <sub>G</sub> =1Ω, I <sub>D</sub> =1A, R <sub>L</sub> =15Ω.	---	12	---	ns
T <sub>r</sub>	Rise Time		---	6	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	38	---	
T <sub>f</sub>	Fall Time		---	9	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, f=1MHz	---	3495	---	pF
C <sub>oss</sub>	Output Capacitance		---	1045	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	62	---	

**Diode Characteristics**

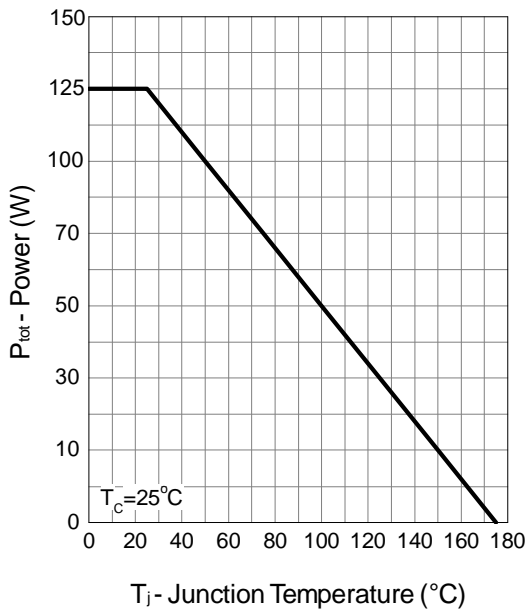
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	55	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>		---	---	160	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A, T <sub>J</sub> =25°C	---	0.8	1.2	V

Note :

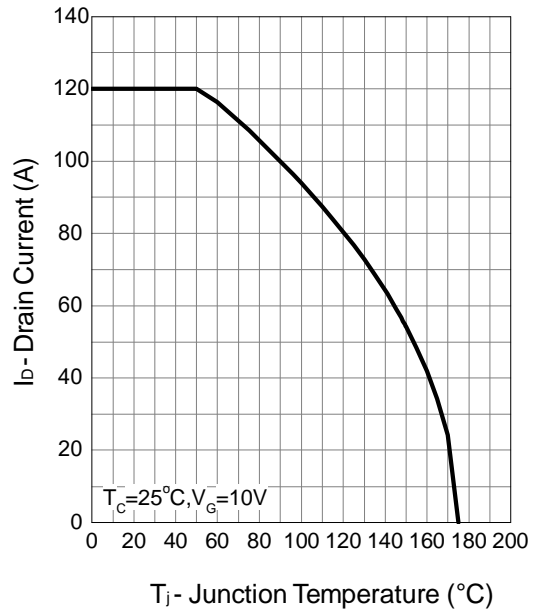
1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper, t<10sec.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
3. The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=20V, V<sub>GS</sub>=10V, L=0.5mH, I<sub>AS</sub>=40A
4. The power dissipation is limited by 150°C junction temperature
5. The Min. value is 100% EAS tested guarantee.
6. The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.
7. Package limitation current is 60A.

**Typical Characteristics**

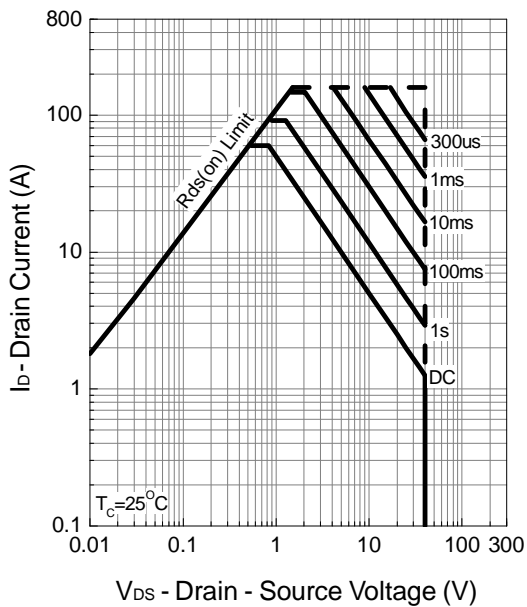
**Power Dissipation**



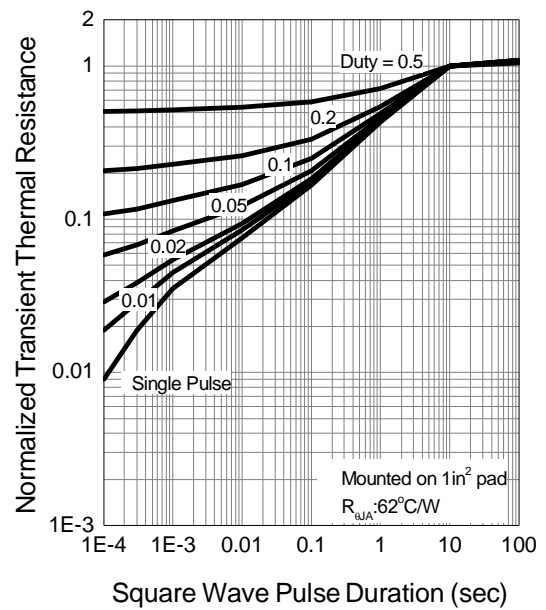
**Drain Current**



**Safe Operation Area**

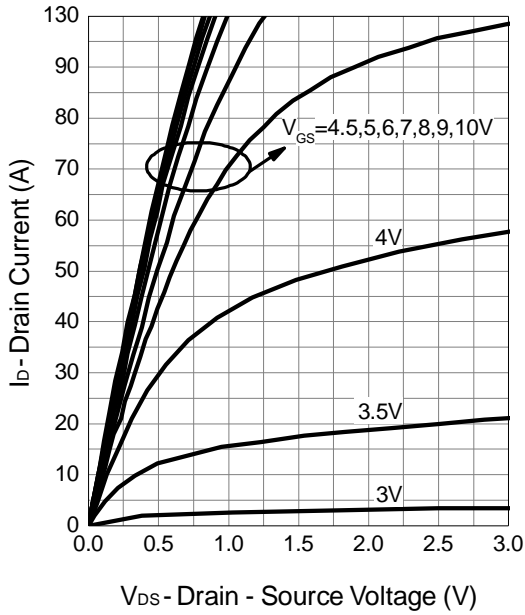


**Thermal Transient Impedance**

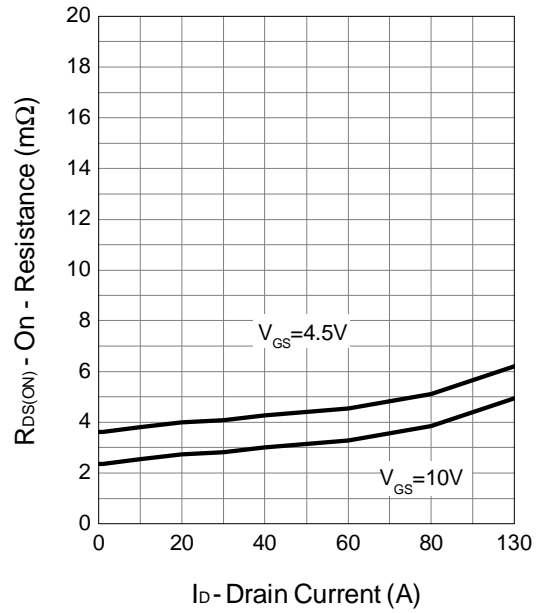


**Typical Characteristics**

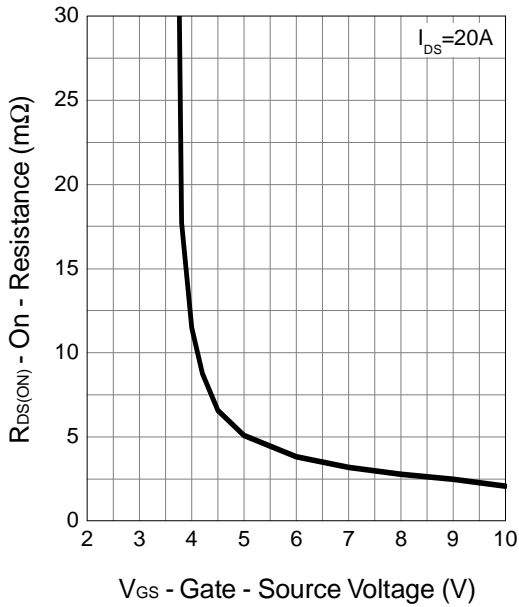
**Output Characteristics**



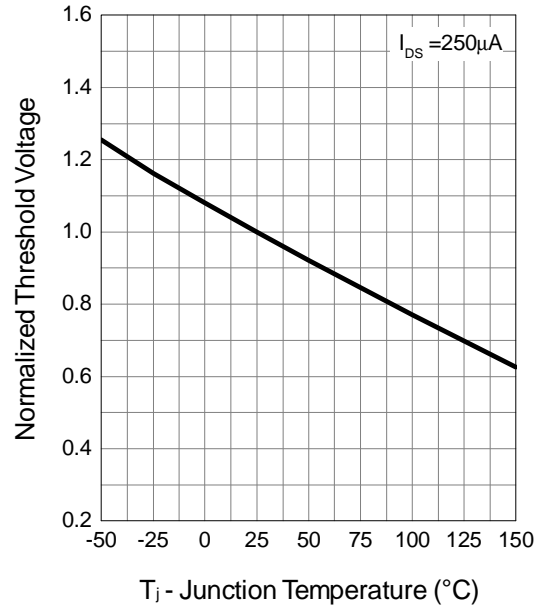
**Drain-Source On Resistance**



**Gate-Source On Resistance**

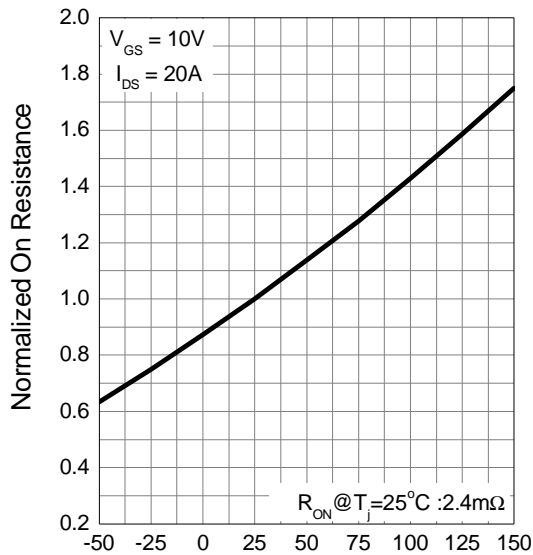


**Gate Threshold Voltage**



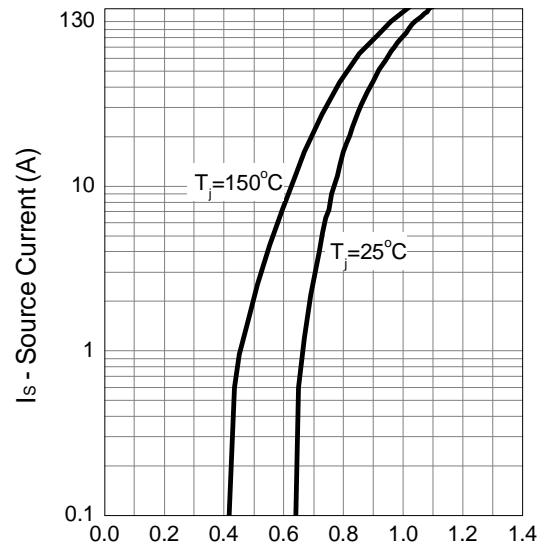
**Typical Characteristics**

**Drain-Source On Resistance**



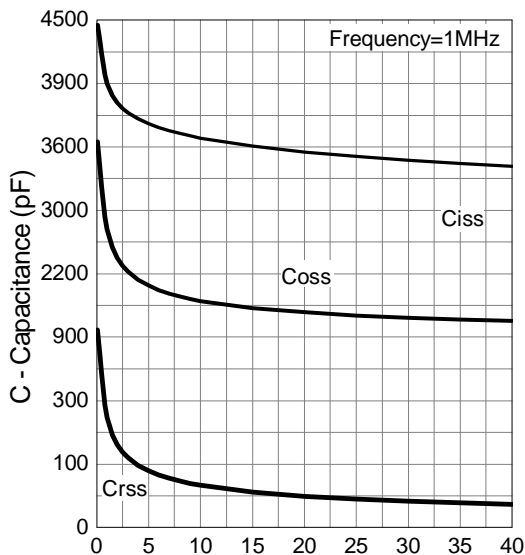
T<sub>j</sub> - Junction Temperature (°C)

**Source-Drain Diode Forward**



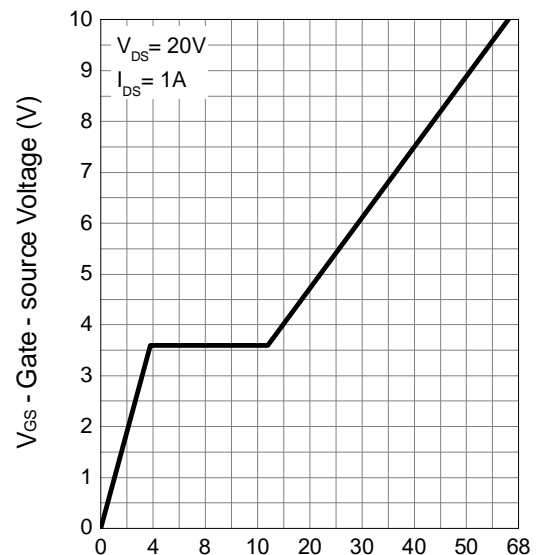
V<sub>SD</sub> - Source - Drain Voltage (V)

**Capacitance**



V<sub>DS</sub> - Drain - Source Voltage (V)

**Gate Charge**



Q<sub>G</sub> - Gate Charge (nC)



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